

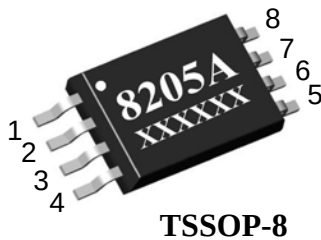
Dual N-Channel High Density Trench MOSFET (20V, 6.0A)

PRODUCT SUMMARY		
V_{DS}	I_D	$R_{DS(on)}$ (m Ω) Max
20V	6.0A	24 @ $V_{GS}=4.0V$, $I_D=6.0A$
		30 @ $V_{GS}=2.5V$, $I_D=5.2A$

Features

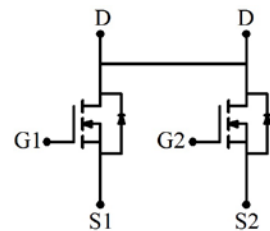
- Advanced Trench Process Technology
- High Density Cell Design for Ultra Low On-Resistance
- Surface mount Package
- Ordering information: GM8205A-G(Lead(Pb)-free and halogen-free)

RoHS+HF



TSSOP-8

Pin 1/ 8: Drain
Pin 2/ 3: Source 1
Pin 4: Gate 1
Pin 5: Gate 2
Pin 6/ 7: Source 2
PKG:TSSOP-8



Absolute Maximum Ratings ($T_A=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Drain Current (Continuous)	6.0	A
I_{DM}	Drain Current (Pulsed) ^a	20	A
P_D	Total Power Dissipation @ $T_A=25^\circ\text{C}$	2.0	W
I_S	Maximum Diode Forward Current	1.7	A
T_j, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (PCB mounted) ^b	62	$^\circ\text{C/W}$

Note: a: Repetitive Rating; Pulse width limited by the maximum junction temperature.

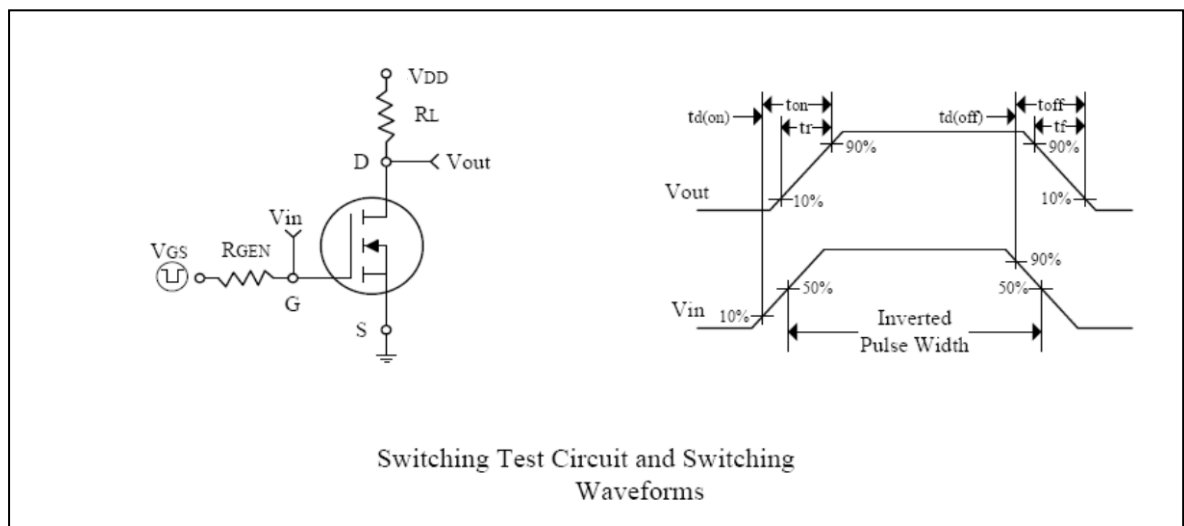
b: 1-in² 2oz Cu PCB board

Electrical Characteristics (T_A=25°C, unless otherwise noted)

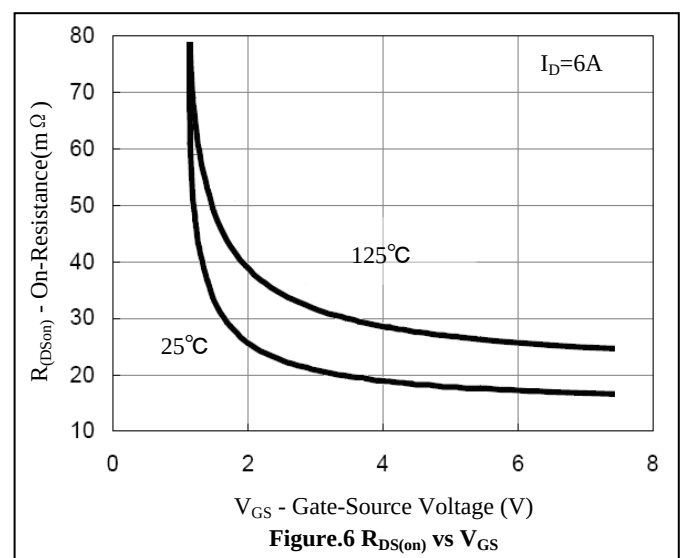
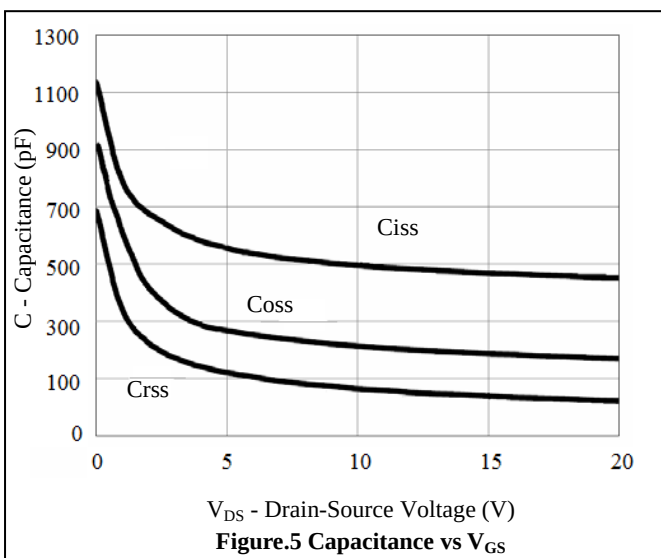
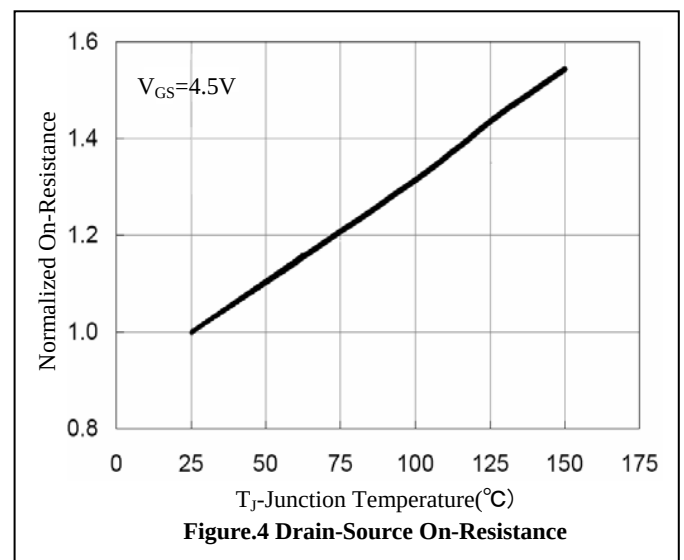
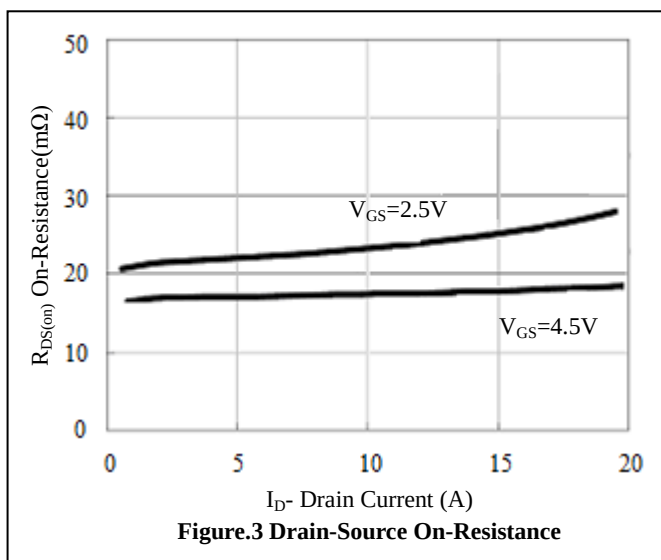
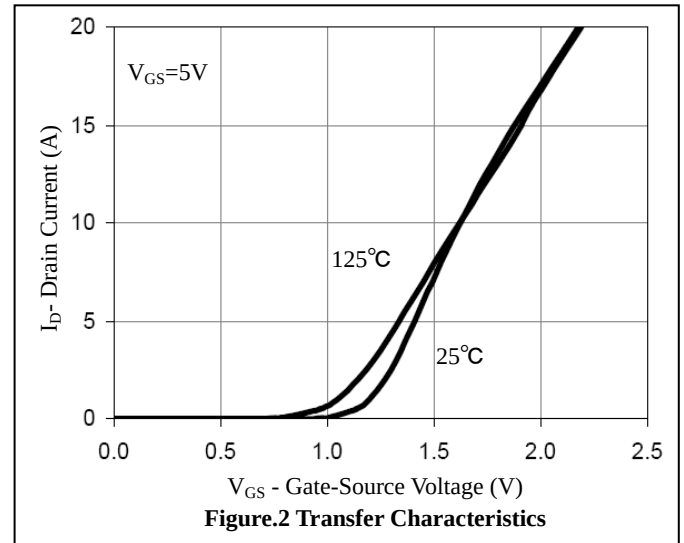
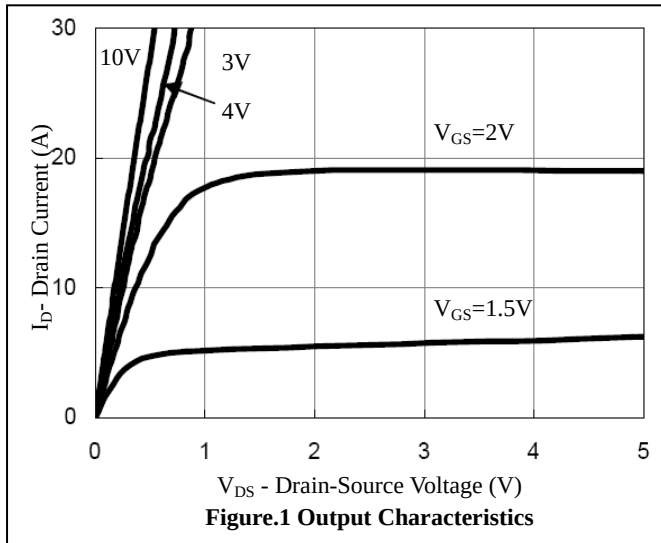
Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
• Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V, V _{GS} =0V	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V	-	-	±100	nA
• On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.6	-	1.2	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =4.0V, I _D =6.0A	-	20	24	mΩ
		V _{GS} =2.5V, I _D =5.2A	-	26	30	
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D =6.0A	-	5	-	S
• Dynamic Characteristic						
C _{iss}	Input Capacitance	V _{DS} =8V, V _{GS} =0V, f=1MHz	-	559	-	PF
C _{oss}	Output Capacitance		-	148	-	
C _{rss}	Reverse Transfer Capacitance		-	127	-	
• Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =10V, I _D =3.0A, V _{GS} =4.5V	-	5	-	nC
Q _{gs}	Gate-Source Charge		-	0.9	-	
Q _{gd}	Gate-Drain Charge		-	1.4	-	
t _{d(on)}	Turn-on Delay Time	V _{DD} =10V, R _L =10Ω, I _D =1A, V _{GS} =10V, R _{GEN} =6Ω	-	10.2	-	nS
t _r	Turn-on Rise Time		-	7	-	
t _{d(off)}	Turn-off Delay Time		-	33	-	
t _f	Turn-off Fall Time		-	6.8	-	
• Drain-Source Diode Characteristics						
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =1.7A	-	-	1.2	V

Note: c : Pulse Test : Pulse Width < 300μs, Duty Cycle < 2%

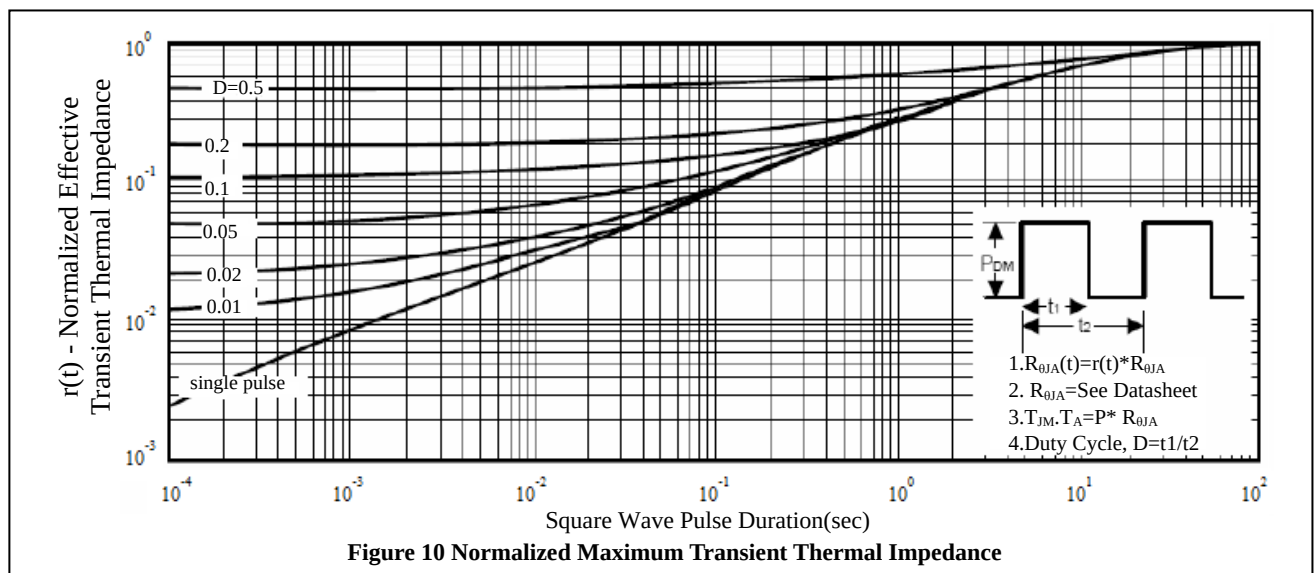
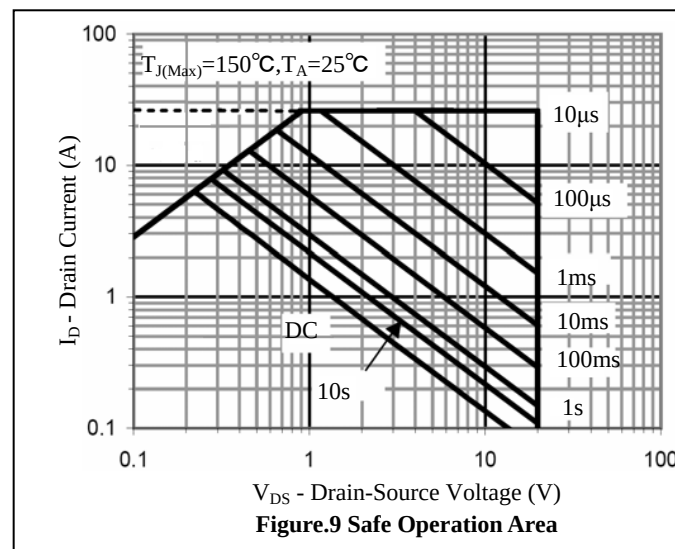
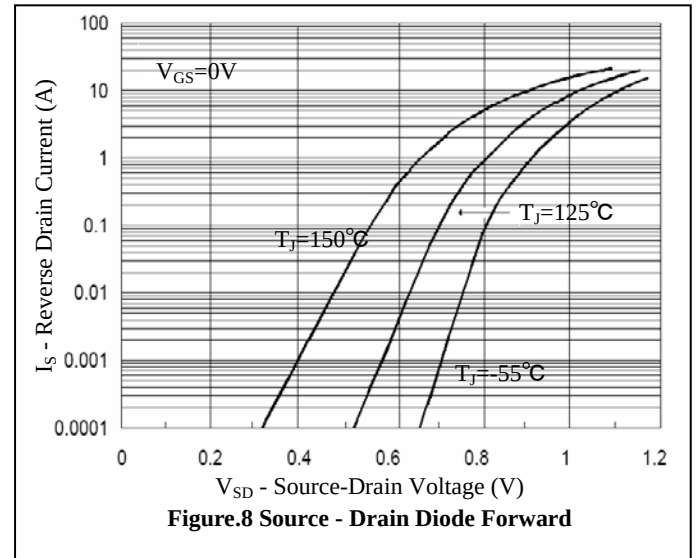
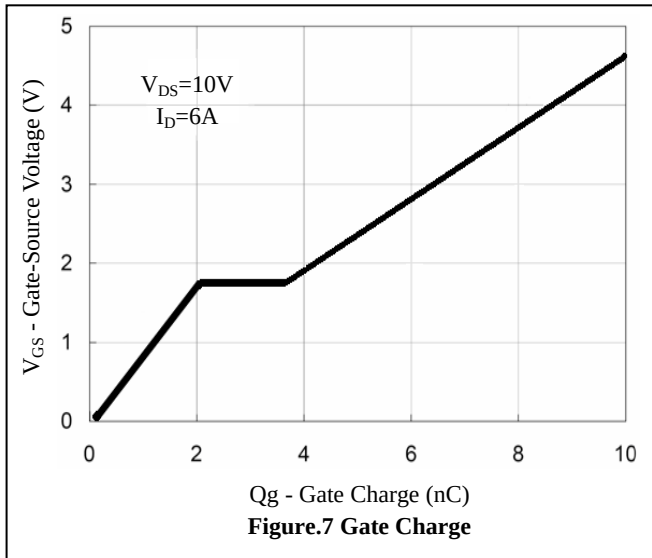
d: Guaranteed by design, not subject to production testing.



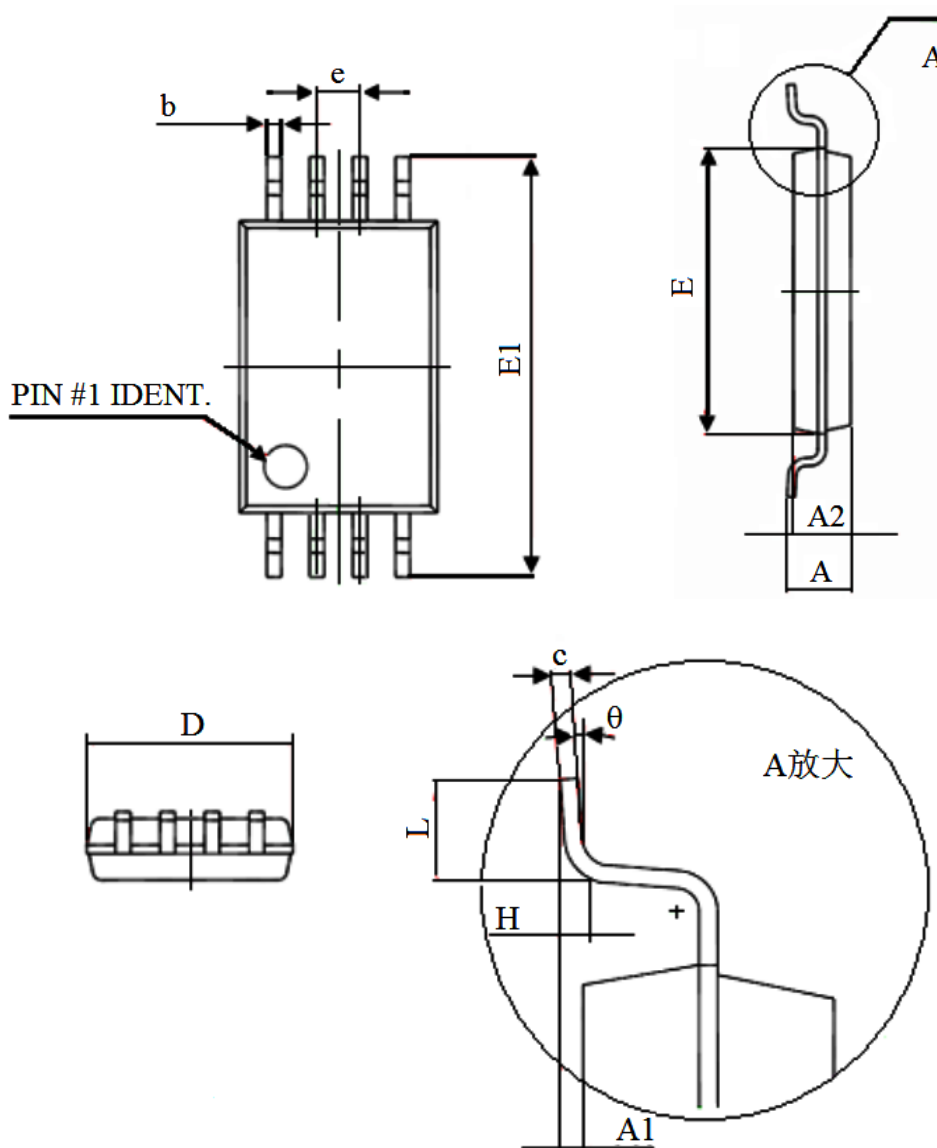
Characteristics Curve



Characteristics Curve



TSSOP-8 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
D	2.900	3.100	0.114	0.122
E	4.300	4.500	0.169	0.177
b	0.190	0.300	0.007	0.012
c	0.090	0.200	0.004	0.008
E1	6.250	6.550	0.246	0.258
A		1.100	0.000	0.043
A2	0.800	1.000	0.031	0.039
A1	0.020	0.150	0.001	0.006
e	0.65 (BSC)		0.050 (BSC)	
L	0.500	1.270	0.020	0.050
H	0.25(TYP)		0.01(TYP)	
θ	1°	7°	1°	7°



Notice

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2. Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.